IC Process

1. P-Type Start Wafer
2. Grow P-Epitaxial Layer
3. Spin Resist Coating
4. Expose N-Well mask
Develop resist

P-EPI

P Substrate

Implant N-Well

P-EPI

P Substrate

Remove resist

P-EPI

P Substrate

Anneal wafer – gives us new oxide layer and diffuses N-Well.
Spin Polyimide
Spin resist
Expose Via 1 mask (vias connect two metals)
Etch Via
Remove resist

Deposit Metal 2 using sputtering
Spin resist
Expose Metal 2 mask
Etch Metal using RIE
Remove resist

Spin Polyimide
Spin resist
Expose Via 2 mask
Etch Via
Remove resist

hole for Metal 3 contact
Deposit Metal 3 using sputtering
Spin resist
Expose Metal 3 mask
Etch Metal using RIE
Remove resist

Spin Polymide
Spin resist
Expose Passivation mask
Etch Poly
Remove resist
Deposit Nitride using CVD
Spin resist
Expose Passivation mask again
Etch Nitride
Remove resist